



CAT25C11/03/05/09/17

1K/2K/4K/8K/16K SPI Serial CMOS EEPROM

FEATURES

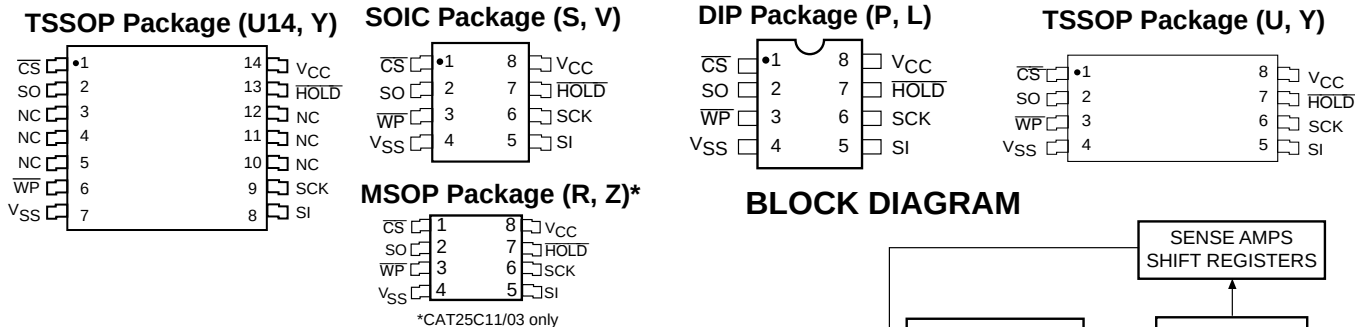
- 10 MHz SPI compatible
- 1.8 to 6.0 volt operation
- Hardware and software protection
- Zero standby current
- Low power CMOS technology
- SPI modes (0,0 & 1,1)*
- Commercial, industrial, automotive and extended temperature ranges
- 1,000,000 program/erase cycles
- 100 year data retention
- Self-timed write cycle
- 8-pin DIP/SOIC, 8/14-pin TSSOP and 8-pin MSOP
- 16/32-byte page write buffer
- Write protection
 - Protect first page, last page, any 1/4 array or lower 1/2 array

DESCRIPTION

The CAT25C11/03/05/09/17 is a 1K/2K/4K/8K/16K-Bit SPI Serial CMOS EEPROM internally organized as 128x8/256x8/512x8/1024x8/2048x8 bits. Catalyst's advanced CMOS Technology substantially reduces device power requirements. The CAT25C11/03/05 features a 16-byte page write buffer. The 25C09/17 features a 32-byte page write buffer. The device operates via the SPI bus serial interface and is enabled through a Chip Select ($\overline{CS}$). In addition to the Chip Select, the clock

input (SCK), data in (SI) and data out (SO) are required to access the device. The $\overline{HOLD}$ pin may be used to suspend any serial communication without resetting the serial sequence. The CAT25C11/03/05/09/17 is designed with software and hardware write protection features including Block Write protection. The device is available in 8-pin DIP, 8-pin SOIC, 8/14-pin TSSOP and 8-pin MSOP packages.

PIN CONFIGURATION

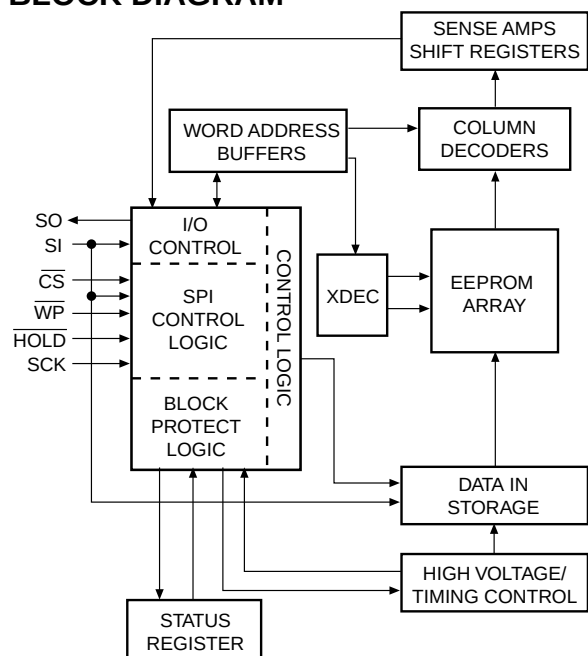


PIN FUNCTIONS

Pin Name	Function
SO	Serial Data Output
SCK	Serial Clock
$\overline{WP}$	Write Protect
VCC	+1.8V to +6.0V Power Supply
VSS	Ground
$\overline{CS}$	Chip Select
SI	Serial Data Input
$\overline{HOLD}$	Suspends Serial Input
NC	No Connect

* Other SPI modes available on request.

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	–55°C to +125°C
Storage Temperature	–65°C to +150°C
Voltage on any Pin with Respect to $V_{SS}^{(1)}$	–2.0V to $+V_{CC} + 2.0V$
V_{CC} with Respect to V_{SS}	–2.0V to +7.0V
Package Power Dissipation Capability ($T_a = 25^\circ\text{C}$)	1.0W
Lead Soldering Temperature (10 secs)	300°C
Output Short Circuit Current ⁽²⁾	100 mA

***COMMENT**

Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.

RELIABILITY CHARACTERISTICS

Symbol	Parameter	Min.	Max.	Units	Reference Test Method
$N_{END}^{(3)}$	Endurance	1,000,000		Cycles/Byte	MIL-STD-883, Test Method 1033
$T_{DR}^{(3)}$	Data Retention	100		Years	MIL-STD-883, Test Method 1008
$V_{ZAP}^{(3)}$	ESD Susceptibility	2000		Volts	MIL-STD-883, Test Method 3015
$I_{LTH}^{(3)(4)}$	Latch-Up	100		mA	JEDEC Standard 17

D.C. OPERATING CHARACTERISTICS

$V_{CC} = +1.8V$ to $+6.0V$, unless otherwise specified.

Symbol	Parameter	Limits			Units	Test Conditions
		Min.	Typ.	Max.		
I_{CC1}	Power Supply Current (Operating Write)			5	mA	$V_{CC} = 5V$ @ 5MHz SO=open; CS= V_{SS}
I_{CC2}	Power Supply Current (Operating Read)			3	mA	$V_{CC} = 5.5V$ $F_{CLK} = 5MHz$
I_{SB}	Power Supply Current (Standby)			0	μA	$\overline{CS} = V_{CC}$ $V_{IN} = V_{SS}$ or V_{CC}
I_{LI}	Input Leakage Current			2	μA	
I_{LO}	Output Leakage Current			3	μA	$V_{OUT} = 0V$ to V_{CC} , CS = 0V
$V_{IL}^{(5)}$	Input Low Voltage	-1		$V_{CC} \times 0.3$	V	
$V_{IH}^{(5)}$	Input High Voltage	$V_{CC} \times 0.7$		$V_{CC} + 0.5$	V	
V_{OL1}	Output Low Voltage			0.4	V	$2.7V \leq V_{CC} < 5.5V$ $I_{OL} = 3.0mA$ $I_{OH} = -1.6mA$
V_{OH1}	Output High Voltage	$V_{CC} - 0.8$			V	
V_{OL2}	Output Low Voltage			0.2	V	$1.8V \leq V_{CC} < 2.7V$ $I_{OL} = 150\mu A$ $I_{OH} = -100\mu A$
V_{OH2}	Output High Voltage	$V_{CC} - 0.2$			V	

Note:

- (1) The minimum DC input voltage is –0.5V. During transitions, inputs may undershoot to –2.0V for periods of less than 20 ns. Maximum DC voltage on output pins is $V_{CC} + 0.5V$, which may overshoot to $V_{CC} + 2.0V$ for periods of less than 20 ns.
- (2) Output shorted for no more than one second. No more than one output shorted at a time.
- (3) This parameter is tested initially and after a design or process change that affects the parameter.
- (4) Latch-up protection is provided for stresses up to 100 mA on address and data pins from –1V to $V_{CC} + 1V$.
- (5) V_{ILMIN} and V_{IHMAX} are reference values only and are not tested.

PIN CAPACITANCE (1)

Applicable over recommended operating range from $T_A=25^{\circ}\text{C}$, $f=1.0\text{ MHz}$, $V_{CC}=\pm 5.0\text{V}$ (unless otherwise noted).

Symbol	Test Conditions	Max.	Units	Conditions
C_{OUT}	Output Capacitance (SO)	8	pF	$V_{OUT}=0\text{V}$
C_{IN}	Input Capacitance ($\overline{CS}$, SCK, SI, $\overline{WP}$, $\overline{HOLD}$)	6	pF	$V_{IN}=0\text{V}$

A.C. CHARACTERISTICS

SYMBOL	PARAMETER	Limits						UNITS	Test Conditions
		1.8V-6.0V		2.5V-6.0V		4.5V-5.5V			
		Min.	Max.	Min.	Max.	Min.	Max.		
t _{SU}	Data Setup Time	50		20		20		ns	C _L = 50pF (note 2)
t _H	Data Hold Time	50		20		20		ns	
t _{WH}	SCK High Time	250		75		40		ns	
t _{WL}	SCK Low Time	250		75		40		ns	
f _{SCK}	Clock Frequency	DC	1	DC	5	DC	10	MHz	
t _{LZ}	$\overline{HOLD}$ to Output Low Z		50		50		50	ns	
t _{RI} ⁽¹⁾	Input Rise Time		2		2		2	μs	
t _{FI} ⁽¹⁾	Input Fall Time		2		2		2	μs	
t _{HD}	$\overline{HOLD}$ Setup Time	100		40		40		ns	
t _{CD}	$\overline{HOLD}$ Hold Time	100		40		40		ns	
t _{WC} ⁽³⁾	Write Cycle Time		10		5		5	ms	
t _V	Output Valid from Clock Low		250		75		40	ns	
t _{HO}	Output Hold Time	0		0		0		ns	
t _{DIS}	Output Disable Time		250		75		75	ns	
t _{HZ}	$\overline{HOLD}$ to Output High Z		150		50		50	ns	
t _{CS}	$\overline{CS}$ High Time	500		100		100		ns	
t _{CSS}	$\overline{CS}$ Setup Time	500		100		100		ns	
t _{CSH}	$\overline{CS}$ Hold Time	500		100		100		ns	
t _{WPS}	$\overline{WP}$ Setup Time	150		50		50		ns	
t _{CSH}	$\overline{CS}$ Hold Time	150		50		50		ns	

(1) This parameter is tested initially and after a design or process change that affects the parameter.

(2) AC Test Conditions:

Input Pulse Voltages: $0.3V_{CC}$ to $0.7V_{CC}$

Input rise and fall times: $\leq 10\text{ns}$

Input and output reference voltages: $0.5V_{CC}$

Output load: current source $I_{OL\text{ max}}$ / $I_{OH\text{ max}}$; $C_L = 50\text{pF}$

(3) t_{WC} is the time from the rising edge of $\overline{CS}$ after a valid write sequence to the end of the internal write cycle.

FUNCTIONAL DESCRIPTION

The CAT25C11/03/05/09/17 supports the SPI bus data transmission protocol. The synchronous Serial Peripheral Interface (SPI) helps the CAT25C11/03/05/09/17 to interface directly with many of today's popular microcontrollers. The CAT25C11/03/05/09/17 contains an 8-bit instruction register. (The instruction set and the operation codes are detailed in the instruction set table)

After the device is selected with $\overline{CS}$ going low, the first byte will be received. The part is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The first byte contains one of the six op-codes that define

the operation to be performed.

PIN DESCRIPTION

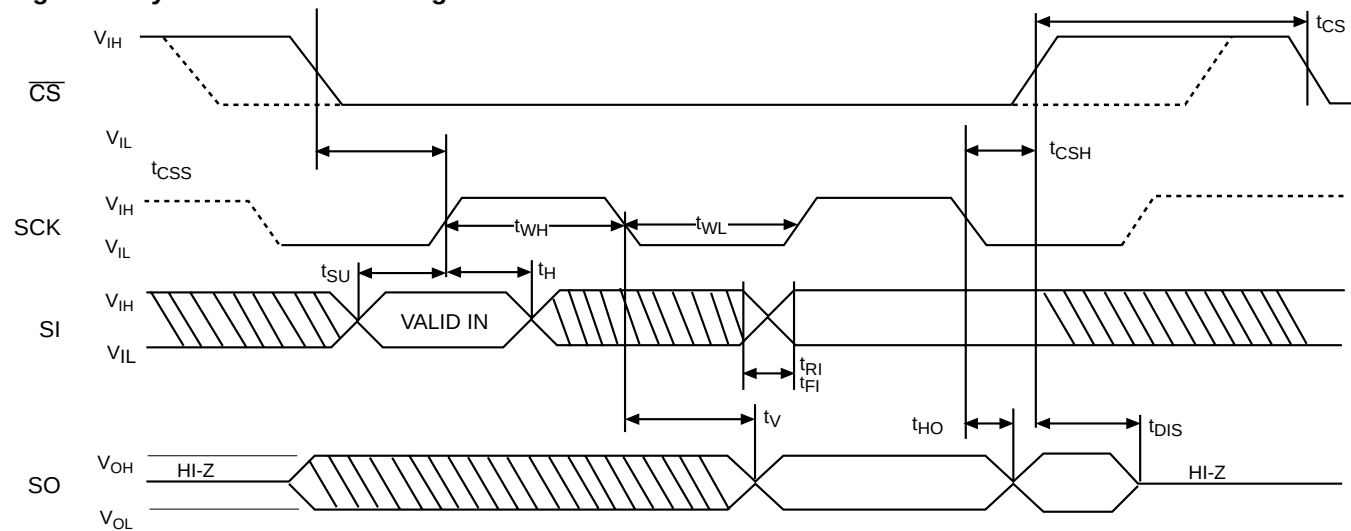
SI: Serial Input

SI is the serial data input pin. This pin is used to input all opcodes, byte addresses, and data to be written to the 25C11/03/05/09/17. Input data is latched on the rising edge of the serial clock for SPI modes (0, 0 & 1, 1).

SO: Serial Output

SO is the serial data output pin. This pin is used to transfer data out of the 25C11/03/05/09/17. During a read cycle, data is shifted out on the falling edge of the serial clock for

Figure 1. Synchronous Data Timing



Note: Dashed Line= mode (1, 1) - - - -

INSTRUCTION SET

Instruction	Opcode	Operation
WREN	0000 0110	Enable Write Operations
WRDI	0000 0100	Disable Write Operations
RDSR	0000 0101	Read Status Register
WRSR	0000 0001	Write Status Register
READ	0000 X011 ⁽¹⁾	Read Data from Memory
WRITE	0000 X010 ⁽¹⁾	Write Data to Memory

Power-Up Timing⁽²⁾⁽³⁾

Symbol	Parameter	Max.	Units
t_{PUR}	Power-up to Read Operation	1	ms
t_{PUW}	Power-up to Write Operation	1	ms

Note:

(1) X=0 for 25C11, 25C03, 25C09, 25C17. X=A8 for 25C05

(2) This parameter is tested initially and after a design or process change that affects the parameter.

(3) t_{PUR} and t_{PUW} are the delays required from the time V_{CC} is stable until the specified operation can be initiated.

SPI modes (0,0 & 1,1).

SCK: Serial Clock

SCK is the serial clock pin. This pin is used to synchronize the communication between the microcontroller and the 25C11/03/05/09/17. Opcodes, byte addresses, or data present on the SI pin are latched on the rising edge of the SCK. Data on the SO pin is updated on the falling edge of the SCK for SPI modes (0,0 & 1,1).

$\overline{CS}$: Chip Select

$\overline{CS}$ is the Chip select pin. $\overline{CS}$ low enables the CAT25C11/03/05/09/17 and $\overline{CS}$ high disables the CAT25C11/03/05/09/17. $\overline{CS}$ high takes the SO output pin to high impedance

and forces the devices into a Standby Mode (unless an internal write operation is underway) The CAT25C11/03/05/09/17 draws ZERO current in the Standby mode. A high to low transition on $\overline{CS}$ is required prior to any sequence being initiated. A low to high transition on $\overline{CS}$ after a valid write sequence is what initiates an internal write cycle.

$\overline{WP}$: Write Protect

$\overline{WP}$ is the Write Protect pin. The Write Protect pin will allow normal read/write operations when held high. When $\overline{WP}$ is tied low and the WPEN bit in the status register is set to "1", all write operations to the status register are inhibited. $\overline{WP}$ going low while $\overline{CS}$ is still low will interrupt a write to the status register. If the internal write cycle as already been initiated, $\overline{WP}$ going low will have no effect on any write

BYTE ADDRESS

Device	Address Significant Bits	Address Don't Care Bits	# Address Clock Pulse
CAT25C11	A6 - A0	A7	8
CAT25C03	A7 - A0	—	8
CAT25C05	A7 - A0 (A8 = X bit from Opcode)	—	8
CAT25C09	A9 - A0	A15 - A10	16
CAT25C17	A10 - A0	A15 - A11	16

STATUS REGISTER

7	6	5	4	3	2	1	0
WPEN	1	1	BP2	BP1	BP0	WEL	$\overline{RDY}$

MEMORY PROTECTION

BP2	BP1	BP0	
0	0	0	Non-Protection
0	0	1	Q1 Protected
0	1	0	Q2 Protected
0	1	1	Q3 Protected
1	0	0	Q4 Protected
1	0	1	H1 Protected
1	1	0	P0 Protected
1	1	1	Pn Protected

	25C11	25C03	25C05	25C09	25C17
Q1	00-1F	00-3F	000-07F	000-0FF	000-1FF
Q2	20-3F	40-7F	080-0FF	100-1FF	200-3FF
Q3	40-5F	80-BF	100-17F	200-2FF	400-5FF
Q4	60-7F	C0-FF	180-1FF	300-3FF	600-7FF
H1	00-3F	00-7F	000-0FF	000-1FF	000-3FF
P0	00-0F	00-0F	000-00F	000-01F	000-01F
Pn	70-7F	F0-FF	1F0-1FF	3E0-3FF	7E0-7FF

WRITE PROTECT ENABLE OPERATION

WPEN	$\overline{WP}$	WEL	Protected Blocks	Unprotected Blocks	Status Register
0	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
X	High	0	Protected	Protected	Protected
X	High	1	Protected	Writable	Writable

operation to the status register. The $\overline{WP}$ pin function is blocked when the WPEN bit is set to 0. Figure 10 illustrates the $\overline{WP}$ timing sequence during a write operation.

HOLD: Hold

$\overline{HOLD}$ is the HOLD pin. The $\overline{HOLD}$ pin is used to pause transmission to the CAT25C11/03/05/09/17 while in the middle of a serial sequence without having to re-transmit entire sequence at a later time. To pause, $\overline{HOLD}$ must be brought low while SCK is low. The SO pin is in a high impedance state during the time the part is paused, and transitions on the SI pins will be ignored. To resume communication, $\overline{HOLD}$ is brought high, while SCK is low. $\overline{HOLD}$ should be held high any time this function is not being used. $\overline{HOLD}$ may be tied high directly to V_{CC} or tied to V_{CC} through a resistor. Figure 9 illustrates hold timing sequence.

STATUS REGISTER

The Status Register indicates the status of the device. The $\overline{RDY}$ (Ready) bit indicates whether the CAT25C11/

03/05/09/17 is busy with a write operation. When set to 1 a write cycle is in progress and when set to 0 the device indicates it is ready. This bit is read only the WEL (Write Enable) bit indicates the status of the write enable latch. When set to 1, the device is in a Write Enable state and when set to 0 the device is in a Write Disable state. The WEL bit can only be set by the WREN instruction and can be reset by the WRDI instruction.

The BP0, BP1 and BP2 bits indicate which part of the memory array is currently protected. These bits are set by the user issuing the WRSR instruction. The user is allowed to protect from one page to as much as half the entire array. Once the three protection bits are set the associated memory can be read but not written until the protection bits are reset. These bits are non volatile.

The WPEN (Write Protect Enable) is an enable bit for the $\overline{WP}$ pin. The $\overline{WP}$ pin and WPEN bit in the status register control the programmable hardware write protect feature. Hardware write protection is enabled when $\overline{WP}$ is low and WPEN bit is set to high. The user cannot write to the status register, (including the block protect bits

Figure 2. WREN Instruction Timing

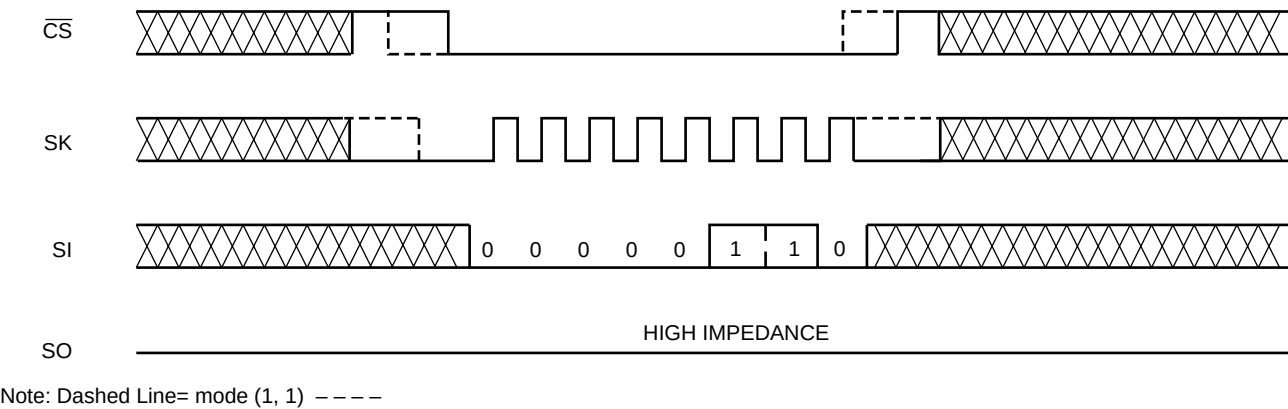
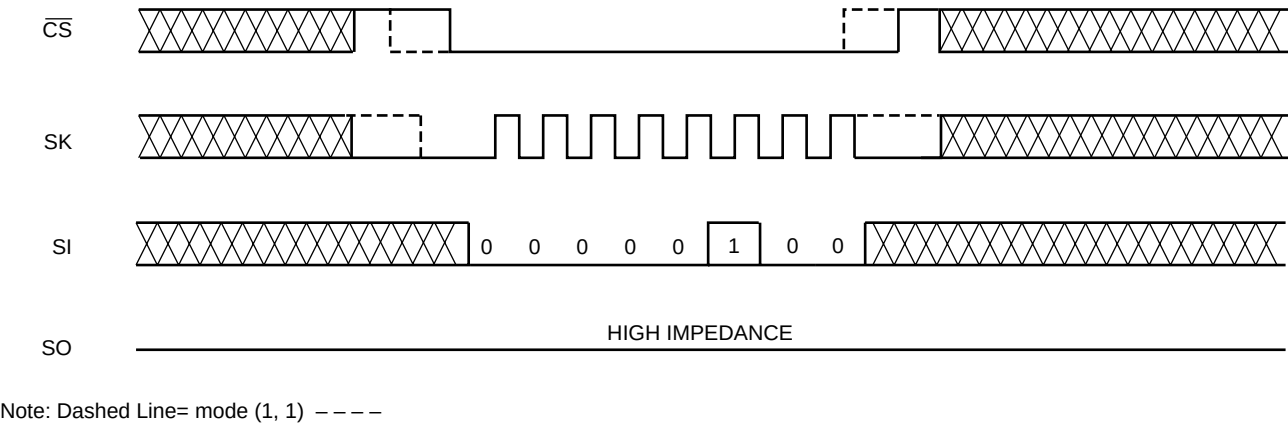


Figure 3. WRDI Instruction Timing



and the WPEN bit) and the block protected sections in the memory array when the chip is hardware write protected. Only the sections of the memory array that are not block protected can be written. Hardware write protection is disabled when either WP pin is high or the WPEN bit is zero.

DEVICE OPERATION

Write Enable and Disable

The CAT25C11/03/05/09/17 contains a write enable latch. This latch must be set before any write operation. The device powers up in a write disable state when V_{CC} is applied. WREN instruction will enable writes (set the latch) to the device. WRDI instruction will disable writes (reset the latch) to the device. Disabling writes will protect the device against inadvertent writes.

READ Sequence

The part is selected by pulling $\overline{CS}$ low. The 8-bit read instruction is transmitted to the CAT25C11/03/05/09/17, followed by the 16-bit address for 25C09/17 (only 10-bit addresses are used for 25C09, 11-bit addresses are used for 25C17. The rest of the bits are don't care bits) and 8-bit address for 25C11/03/05 (for the 25C05, bit 3 of the read data instruction contains address A8).

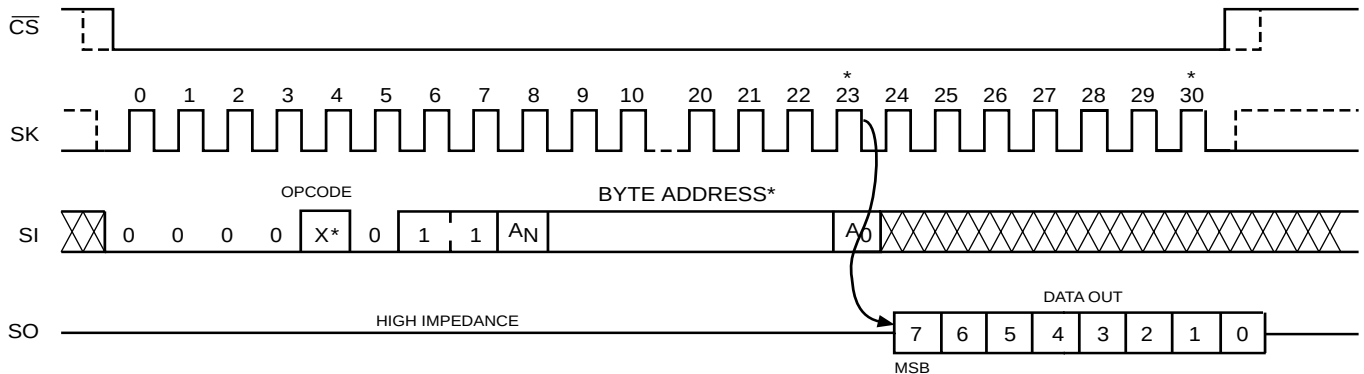
After the correct read instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. The data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses. The internal address pointer is automatically incremented to the next higher address after each byte of data is shifted out. When the highest address is reached, the address counter rolls over to 0000h allowing the read cycle to be continued indefinitely.

The read operation is terminated by pulling the $\overline{CS}$ high. Read sequence is illustrated in Figure 4. Reading status register is illustrated in Figure 5. To read the status register, RDSR instruction should be sent. The contents of the status register are shifted out on the SO line. If a non-volatile write is in progress, the RDSR instruction returns a high on SO. When the non-volatile write cycle is completed, the status register data is read out.

WRITE Sequence

The CAT25C11/03/05/09/17 powers up in a Write Disable state. Prior to any write instructions, the WREN instruction must be sent to CAT25C11/03/05/09/17. The device goes into Write enable state by pulling the $\overline{CS}$ low and then clocking the WREN instruction into CAT25C11/03/05/09/17. The $\overline{CS}$ must be brought high

Figure 4. Read Instruction Timing



*Please check the Byte Address Table.

*X = 0 for CAT25C11, CAT25C03, CAT25C09 and CAT25C17; X = A8 for CAT25C05.

Note: Dashed Line= mode (1, 1) - - - -

enable latch will not have been properly set. Also, for a successful write operation the address of the memory location(s) to be programmed must be outside the protected address field.

Byte Write

Once the device is in a Write Enable state, the user may proceed with a write sequence by setting the $\overline{CS}$ low, issuing a write instruction via the SI line, followed by the 16-bit address for 25C09/17. (only 10-bit addresses are used for 25C09, 11-bit addresses are used for 25C17. The rest of the bits are don't care bits) and 8-bit address for 25C11/03/05 (for the 25C05, bit 3 of the read data instruction contains address A8). Programming will start after the $\overline{CS}$ is brought high. Figure 6 illustrates byte write sequence.

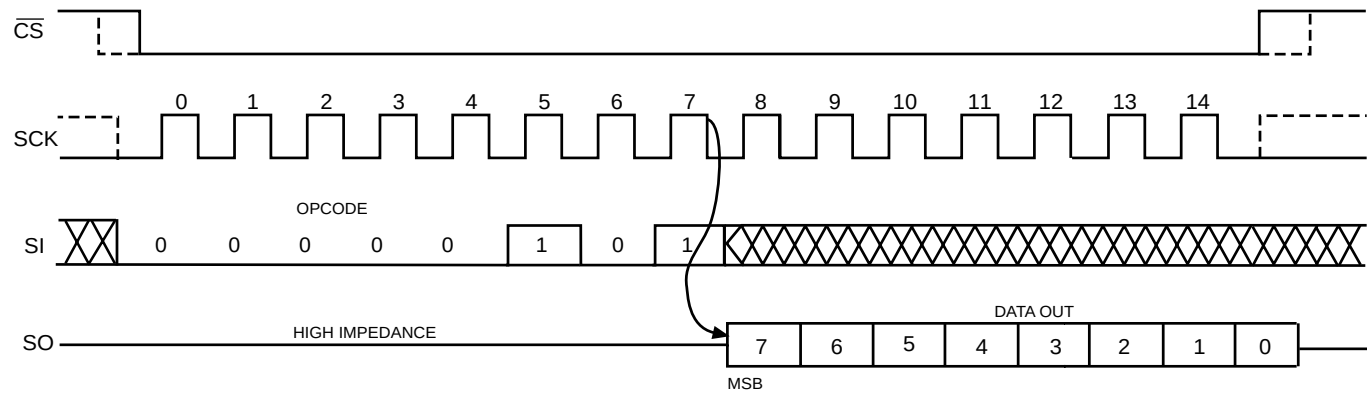
Page Write

The CAT25C11/03/05/09/17 features page write capability. After the initial byte, the host may continue to write after the WREN instruction to enable writes to the

device. If the write operation is initiated immediately after the WREN instruction without $\overline{CS}$ being brought high, the data will not be written to the array because the write up to 16 bytes of data to the CAT25C11/03/05 and 32 bytes of data for 25C09/17. After each byte of data received, lower order address bits are internally incremented by one; the high order bits of address will remain constant. The only restriction is that the X (X=16 for 25C11/03/05 and X=32 for 25C09/17) bytes must reside on the same page. If the address counter reaches the end of the page and clock continues, the counter will “roll over” to the first address of the page and overwrite any data that may have been written. The CAT25C11/03/05/09/17 is automatically returned to the write disable state at the completion of the write cycle. Figure 8 illustrates the page write sequence.

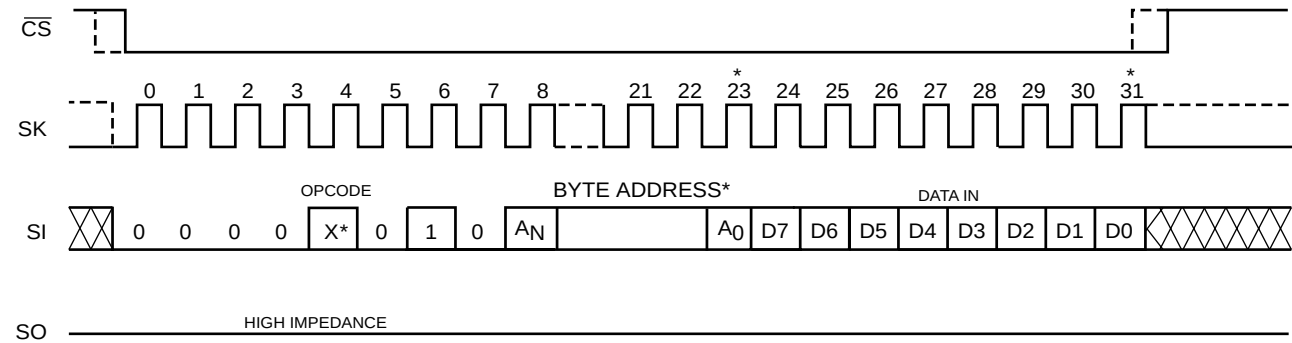
To write to the status register, the WRSR instruction should be sent. Only Bit 2, Bit 3, Bit 4 and Bit 7 of the status register can be written using the write status register instruction. Figure 7 illustrates the sequence of writing to status register.

Figure 5. RDSR Instruction Timing



Note: Dashed Line= mode (1, 1) - - - -

Figure 6. Write Instruction Timing



*Please check the Byte Address Table
X = 0 for CAT25C11, CAT25C03, CAT25C09 and CAT25C17; X = A8 for CAT25C05

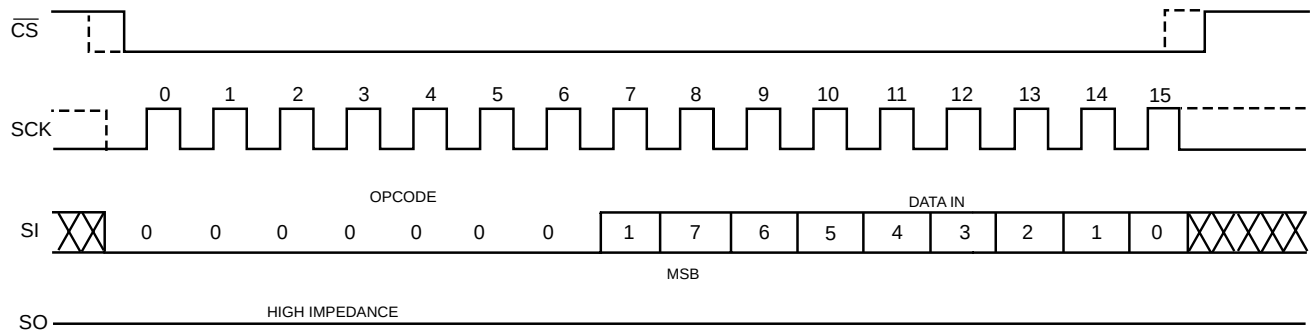
Note: Dashed Line= mode (1, 1) - - - -

DESIGN CONSIDERATIONS

The CAT25C11/03/05/09/17 powers up in a write disable state and in a low power standby mode. A WREN instruction must be issued to perform any writes to the device after power up. Also, on power up $\overline{CS}$ should be brought low to enter a ready state and receive an instruction. After a successful byte/page write or status register write the CAT25C11/03/05/09/17 goes into a write disable mode. $\overline{CS}$ must be set high after the proper

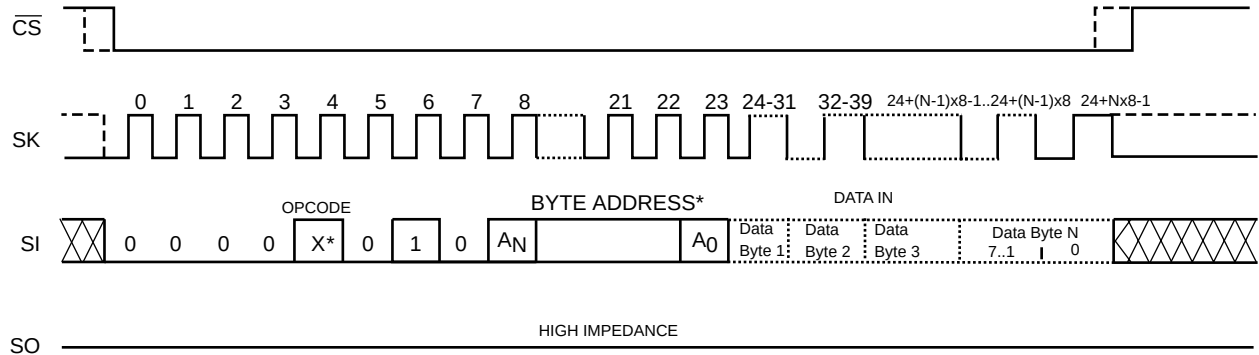
number of clock cycles to start an internal write cycle. Access to the array during an internal write cycle is ignored and programming is continued. On power up, SO is in a high impedance. If an invalid op code is received, no data will be shifted into the CAT25C11/03/05/09/17, and the serial output pin (SO) will remain in a high impedance state until the falling edge of $\overline{CS}$ is detected again.

Figure 7. WRSR Instruction Timing



Note: Dashed Line= mode (1, 1) - - - -

Figure 8. Page Write Instruction Timing



*Please check the Byte Address Table.

*X = 0 for CAT25C11, CAT25C03, CAT25C09 and CAT25C17; X = A8 for CAT25C05

Note: Dashed Line= mode (1, 1) - - - -

Figure 9. **HOLD** Timing

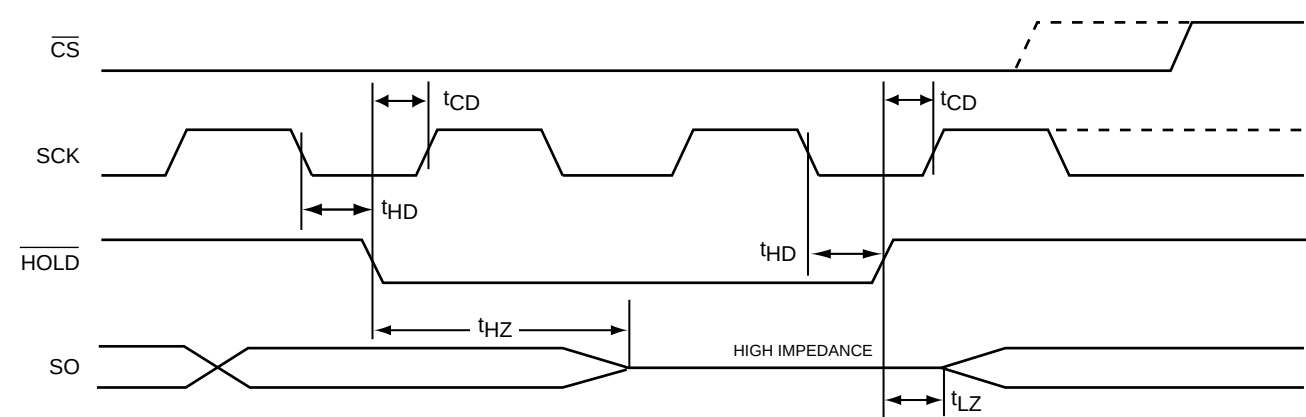
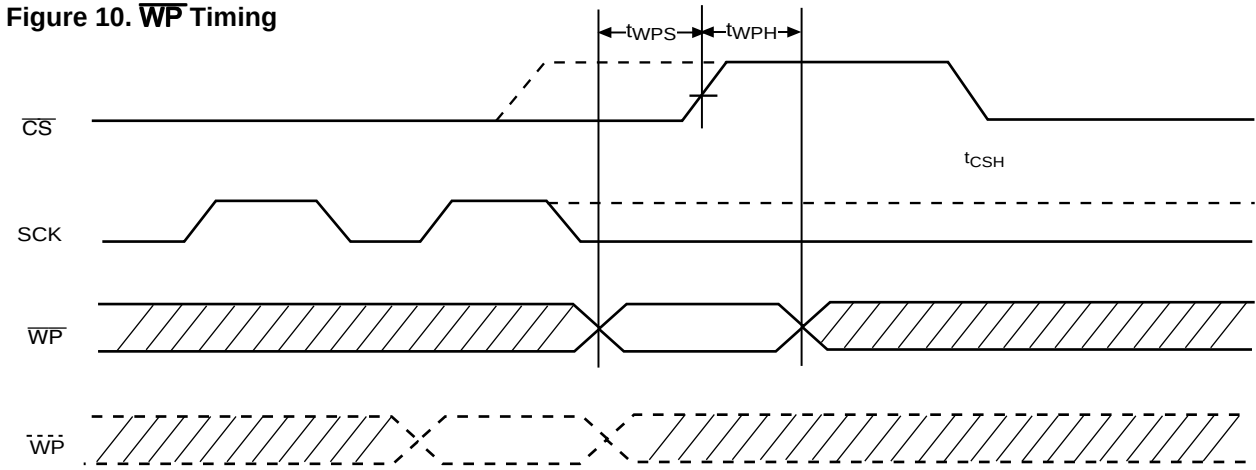
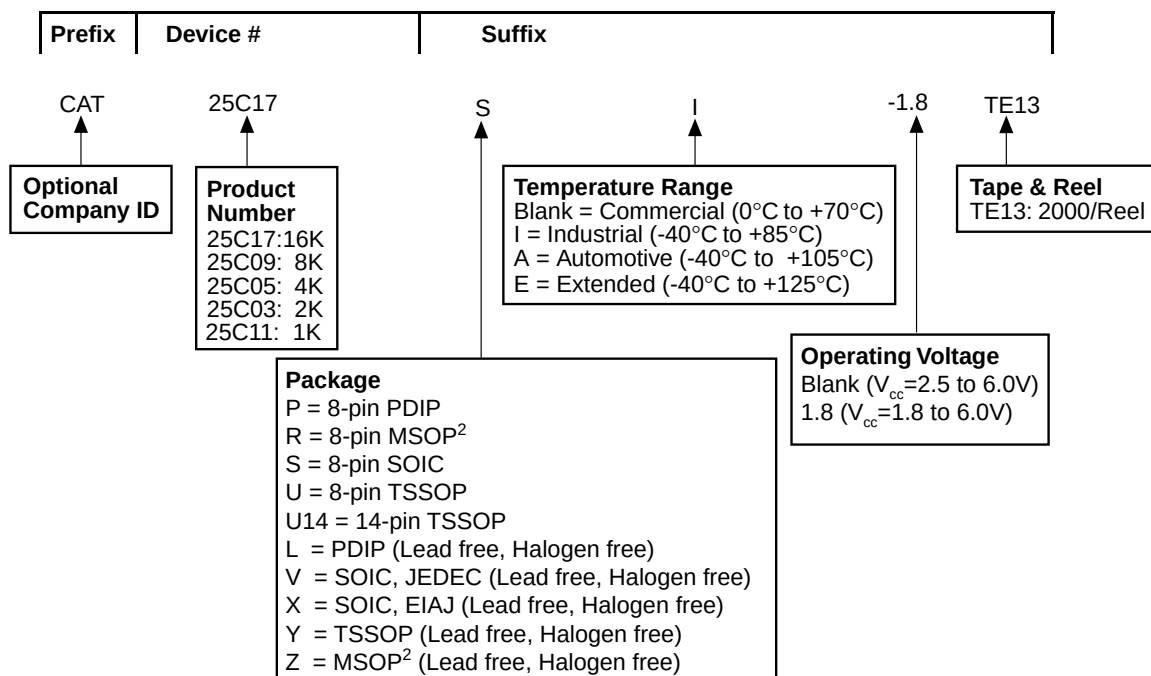


Figure 10. **WP** Timing



Note: Dashed Line= mode (1, 1) -----

ORDERING INFORMATION



Notes:

- (1) The device used in the above example is a 25C17SI-1.8TE13 (SOIC, Industrial Temperature, 1.8 Volt to 6 Volt Operating Voltage, Tape & Reel)
- (2) CAT25C11 and CAT25C03 only.

Copyrights, Trademarks and Patents

Trademarks and registered trademarks of Catalyst Semiconductor include each of the following:

DPP™ DPPs™ AE²™

Catalyst Semiconductor has been issued U.S. and foreign patents and has patent applications pending that protect its products. For a complete list of patents issued to Catalyst Semiconductor contact the Company's corporate office at 408.542.1000.

CATALYST SEMICONDUCTOR MAKES NO WARRANTY, REPRESENTATION OR GUARANTEE, EXPRESS OR IMPLIED, REGARDING THE SUITABILITY OF ITS PRODUCTS FOR ANY PARTICULAR PURPOSE, NOR THAT THE USE OF ITS PRODUCTS WILL NOT INFRINGE ITS INTELLECTUAL PROPERTY RIGHTS OR THE RIGHTS OF THIRD PARTIES WITH RESPECT TO ANY PARTICULAR USE OR APPLICATION AND SPECIFICALLY DISCLAIMS ANY AND ALL LIABILITY ARISING OUT OF ANY SUCH USE OR APPLICATION, INCLUDING BUT NOT LIMITED TO, CONSEQUENTIAL OR INCIDENTAL DAMAGES.

Catalyst Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Catalyst Semiconductor product could create a situation where personal injury or death may occur.

Catalyst Semiconductor reserves the right to make changes to or discontinue any product or service described herein without notice. Products with data sheets labeled "Advance Information" or "Preliminary" and other products described herein may not be in production or offered for sale.

Catalyst Semiconductor advises customers to obtain the current version of the relevant product information before placing orders. Circuit diagrams illustrate typical semiconductor applications and may not be complete.



CATALYST

Catalyst Semiconductor, Inc.
Corporate Headquarters
1250 Borregas Avenue
Sunnyvale, CA 94089
Phone: 408.542.1000
Fax: 408.542.1200
www.catalyst-semiconductor.com

Publication #: 1017
Revision: F
Issue date: 9/24/02
Type: Final